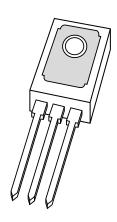
DISCRETE SEMICONDUCTORS

DATA SHEET



BD330PNP power transistor

Product specification Supersedes data of September 1994 File under Discrete Semiconductors, SC04 1997 Apr 22





PNP power transistor

BD330

FEATURES

- High current (max. 3 A)
- Low voltage (max. 20 V).

APPLICATIONS

• Power switching and amplification, especially in portable equipment or e.g. car radio output stages.

DESCRIPTION

PNP power transistor in a TO-126; SOT32 plastic package. NPN complement: BD329.

PINNING

PIN	DESCRIPTION
1	emitter
2	collector, connected to metal part of mounting surface
3	base

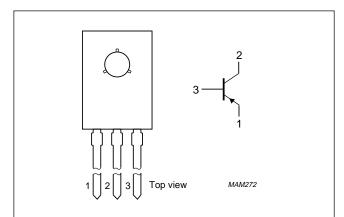


Fig.1 Simplified outline (TO-126; SOT32) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	_	-32	V
V _{CEO}	collector-emitter voltage	open base	_	_	-20	V
I _{CM}	peak collector current		_	_	-3	Α
P _{tot}	total power dissipation	T _{mb} ≤ 45 °C	_	_	15	W
h _{FE}	DC current gain	$I_C = -0.5 \text{ A}; V_{CE} = -1 \text{ V}$	85	_	375	
f _T	transition frequency	$I_C = -50 \text{ mA}; V_{CE} = -5 \text{ V}; f = 100 \text{ MHz}$	_	100	_	MHz

PNP power transistor

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-32	V
V _{CEO}	collector-emitter voltage	open base	_	-20	V
V _{EBO}	emitter-base voltage	open collector	_	- 5	V
I _C	collector current (DC)		_	-3	А
I _{CM}	peak collector current		_	-3	Α
I _{BM}	peak base current		_	-1	Α
P _{tot}	total power dissipation	T _{mb} ≤ 45 °C	_	15	W
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	in free air	100	K/W
R _{th j-mb}	R _{th j-mb} thermal resistance from junction to mounting base		7	K/W

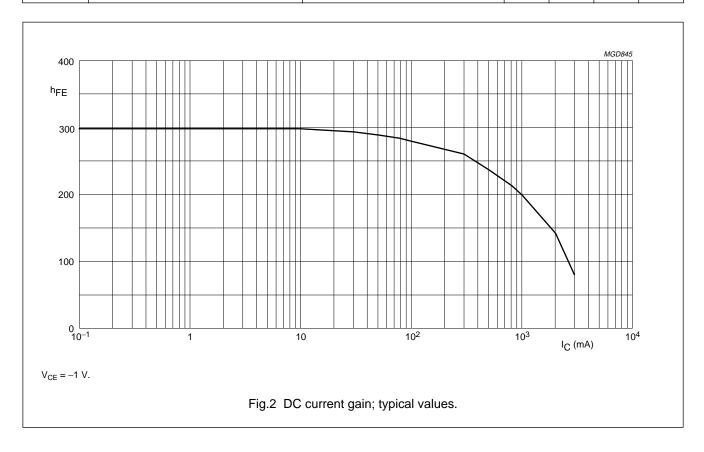
PNP power transistor

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CHARACTERISTICS

 $T_j = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = -32 V	_	_	-100	nA
		$I_E = 0$; $V_{CB} = -32$ V; $T_j = 150$ °C	_	_	-10	μΑ
I _{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -5 V$	_	_	-100	nA
h _{FE}	DC current gain	$I_C = -5 \text{ mA}; V_{CE} = -10 \text{ V}$	50	_	_	
		$I_C = -0.5 \text{ A}; V_{CE} = -1 \text{ V}; \text{ see Fig.2}$	85	_	375	
		$I_C = -2 \text{ A}; V_{CE} = -1 \text{ V}; \text{ see Fig.2}$	40	_	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -2 \text{ A}; I_B = -0.2 \text{ A}$	_	_	-0.5	V
V_{BE}	base-emitter voltage	$I_C = -5 \text{ mA}; V_{CE} = -10 \text{ V}$	_	-600	_	mV
		$I_C = -2 \text{ A}; V_{CE} = -1 \text{ V}$	_	_	-1.2	٧
f _T	transition frequency	$I_C = -50 \text{ mA}; V_{CE} = -5 \text{ V};$ f = 100 MHz	_	100	_	MHz

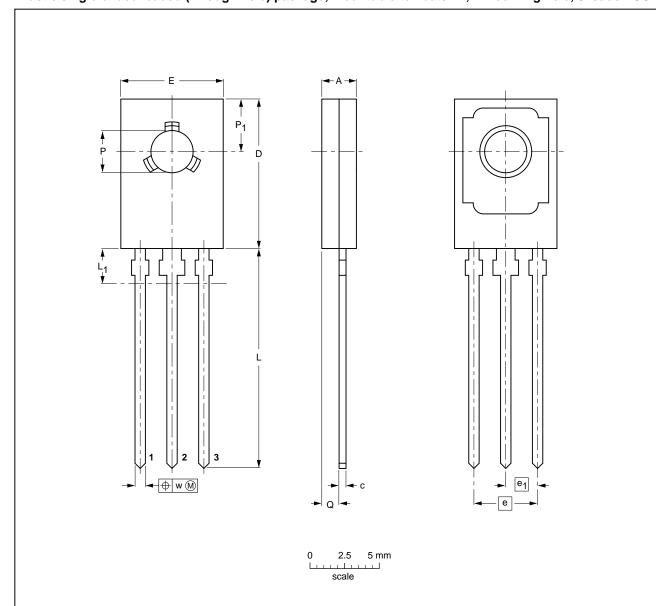


PNP power transistor

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PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; mountable to heatsink, 1 mounting hole; 3 leads SOT32



DIMENSIONS (mm are the original dimensions)

UNI	ГА	bp	С	D	E	е	e ₁	L	L ₁ ⁽¹⁾ max	Q	Р	P ₁	w
mm	2.7 2.3	0.88 0.65	0.60 0.45	11.1 10.5	7.8 7.2	4.58	2.29	16.5 15.3	2.54	1.5 0.9	3.2 3.0	3.9 3.6	0.254

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFERENCES				ISSUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT32		TO-126				97-03-04

PNP power transistor

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DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	

Limiting values

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

PNP power transistor

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